Vishay Semiconductors





SlimSMA (DO-221AC)

PRODUCT SUMMARY					
Package	DO-221AC (SlimSMA)				
I _{F(AV)}	2 A				
V _R	100 V				
V _F at I _F	0.93 V				
t _{rr}	25 ns				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- Hyperfast recovery time, reduced Qrr, and soft recovery
- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		100	V		
Average rectified forward current	I _{F(AV)}	$T_{\rm C} = 155 \ ^{\circ}{\rm C}^{(1)}$	2	А		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	65	A		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

Note

⁽¹⁾ Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	100	-	-	
Forward voltage	VF	I _F = 2 A	-	0.85	0.93	V
i orward voltage	۷F	I _F = 2 A, T _J = 125 °C	-	0.72	0.77	
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	2	
Reverse leakage current IR	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	0.5	8	μA
Junction capacitance	CT	V _R = 100 V	-	10	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		-	25	-	20	
Reverse recovery time	+	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	17	-	ns	
		T _J = 125 °C		-	24	-		
Pools recovery ourrent	1	T _J = 25 °C	I _F = 2 A dI _F /dt = 200 A/μs V _R = 160 V	-	2	-	А	
Peak recovery current	recovery current I _{RRM}	T _J = 125 °C		-	3	-	~	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	17	-	nC	
	T _J = 125 °C		-	37	-			

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. TYP. MAX.		MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	12	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	115	0/11	
Approximate weight				0.03		g	
Approximate weight				0.0011		oz.	
Marking device		Case style SlimSMA (DO-221AC)		21	-11		

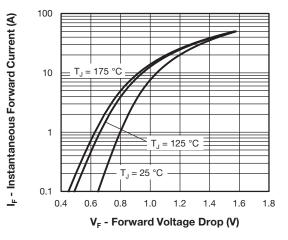
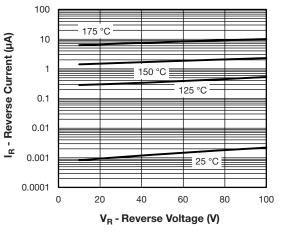
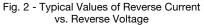


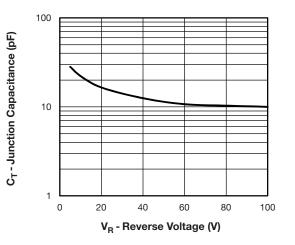
Fig. 1 - Typical Forward Voltage Drop Characteristics







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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

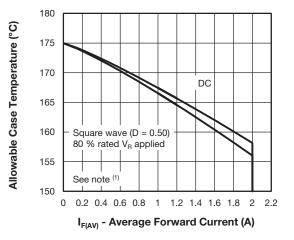


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

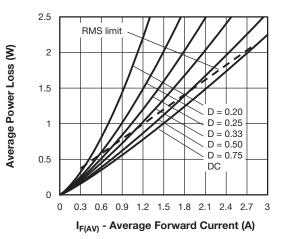


Fig. 5 - Forward Power Loss Characteristics

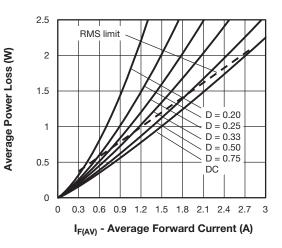
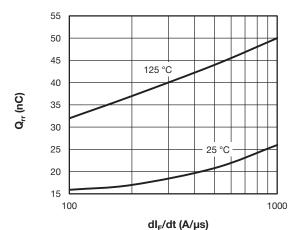


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt



. . . .

Fig. 7 - Typical Stored Charge vs. dI_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see Fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

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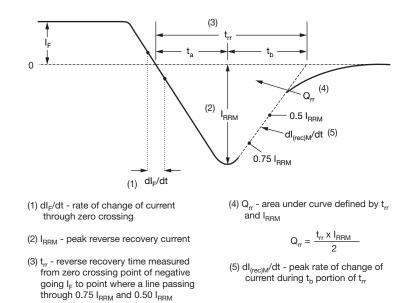


Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device code	VS-	2	Е	J	н	01	Н	M3
	1	2	3	4	5	6	7	8
	1 ·	- Visl	nay Sen	niconduo	ctors pro	oduct		
	2 -	- Cur	rent rati	ng (2 = 2	2 A)			
	3 -	- Circ	cuit conf	iguratior	า:			
		E =	single o	liode				
	4 -	. J=	SlimSM	A packa	ige			
	5 -	- Pro	cess typ	be,				
		H =	hyperfa	st recov	very			
	6 -	- Vol	age coo	de (01 =	100 V)			
	7 -	. Н=	AEC-Q	101 qua	lified			
	8 -	- M3	= halog	en-free,	RoHS-	complia	nt, and	termina

extrapolated to zero current.

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-2EJH01HM3/6A	3500	3500	7"diameter plastic tape and reel				
VS-2EJH01HM3/6B	14 000	14 000	13"diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95771					
Part marking information	www.vishay.com/doc?95562				
Packaging information	www.vishay.com/doc?88869				

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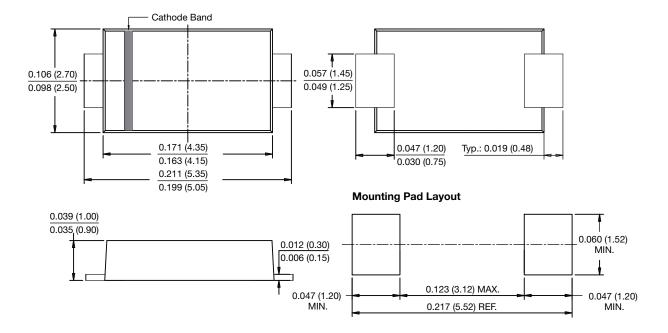
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DO-221AC (SlimSMA)

DIMENSIONS in inches (millimeters)





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